



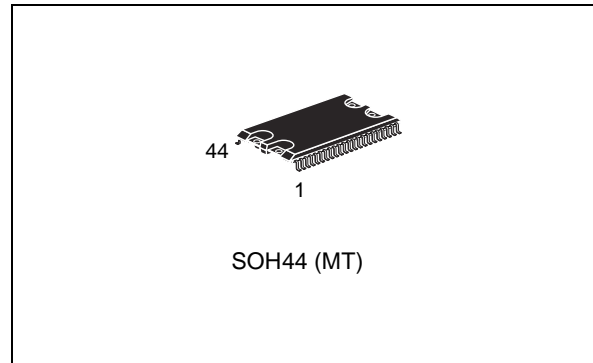
# M48Z32V

## 3.3V, 256 Kbit (32 Kbit x 8) ZEROPOWER<sup>®</sup> SRAM

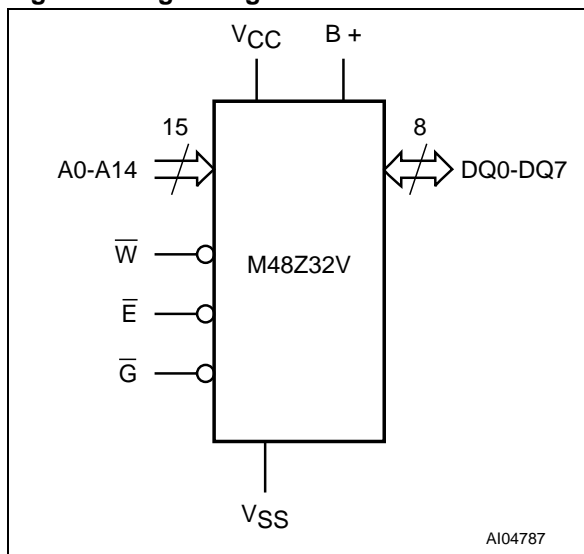
### FEATURES SUMMARY

- INTEGRATED, ULTRA LOW POWER SRAM, and POWER-FAIL CONTROL CIRCUIT
- READ CYCLE TIME EQUALS WRITE CYCLE TIME
- AUTOMATIC POWER-FAIL CHIP DESELECT and WRITE PROTECTION
- WRITE PROTECT VOLTAGES:  
( $V_{PFD}$  = Power-fail Deselect Voltage)  
– M48Z32V:  $2.7V \leq V_{PFD} \leq 3.0V$
- ULTRA-LOW STANDBY CURRENT

**Figure 2. 44-pin, Hatless SOIC Package**



**Figure 1. Logic Diagram**



**Table 1. Signal Names**

A0-A14	Address Inputs
DQ0-DQ7	Data Inputs / Outputs
$\bar{E}$	Chip Enable Input
$\bar{G}$	Output Enable Input
$\bar{W}$	WRITE Enable Input
$V_{CC}$	Supply Voltage
$V_{SS}$	Ground
B +	Positive Battery Pin
NC	Not Connected

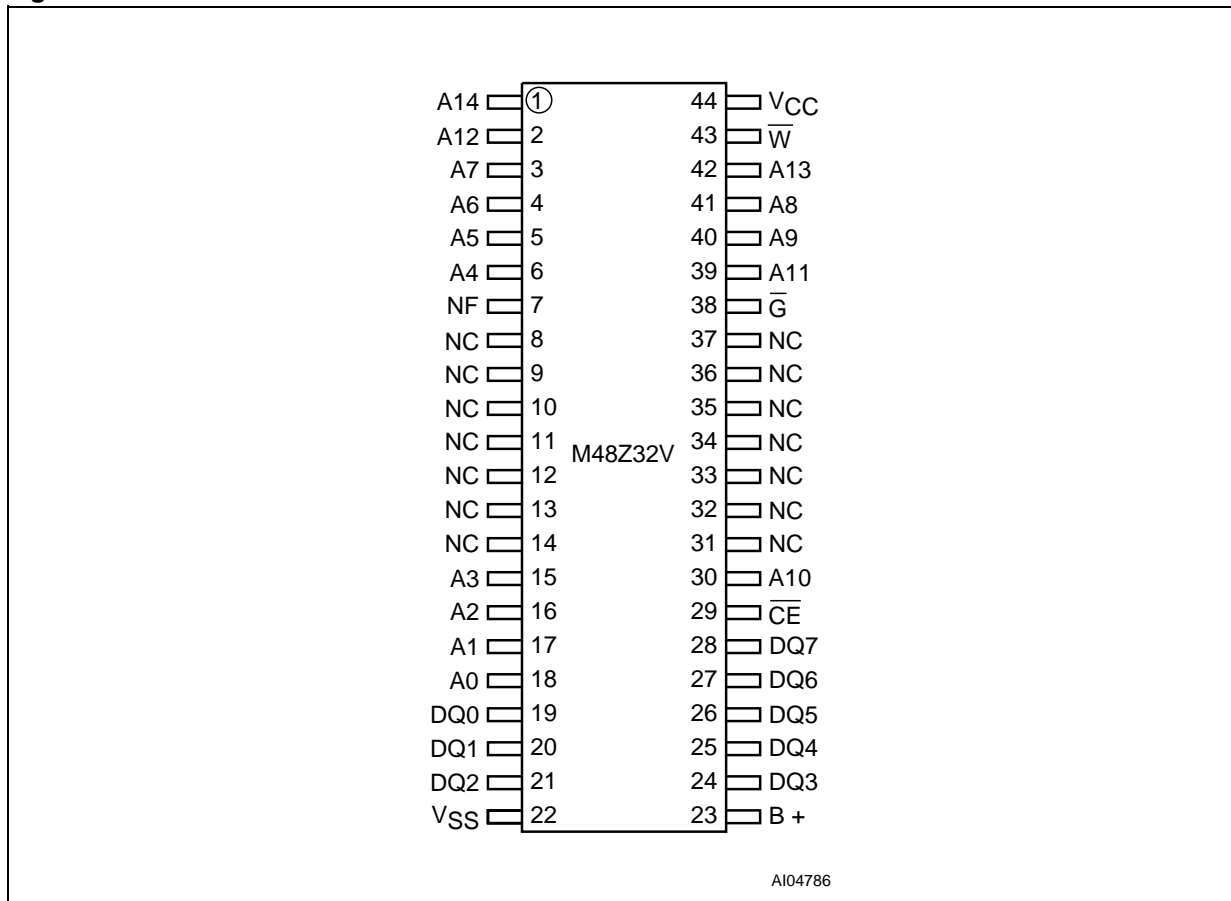
**TABLE OF CONTENTS**

<b>DESCRIPTION</b> .....	<b>3</b>
SOIC Connections (Figure 3.) .....	3
Block Diagram (Figure 4.) .....	4
<b>MAXIMUM RATING.</b> .....	<b>4</b>
Absolute Maximum Ratings (Table 2.) .....	4
<b>DC AND AC PARAMETERS.</b> .....	<b>5</b>
Operating and AC Measurement Conditions (Table 3.) .....	5
AC Measurement Load Circuit (Figure 5.) .....	5
Capacitance (Table 4.) .....	5
DC Characteristics (Table 5.) .....	6
<b>OPERATING MODES</b> .....	<b>6</b>
Operating Modes (Table 6.) .....	6
READ Mode. ....	7
READ Mode AC Waveforms (Figure 6.) .....	7
READ Mode AC Characteristics (Table 7.) .....	8
WRITE Mode. ....	9
WRITE Enable Controlled, WRITE Mode AC Waveforms (Figure 7.) .....	9
Chip Enable Controlled, WRITE Mode AC Waveforms (Figure 8.) .....	9
WRITE Mode AC Characteristics (Table 8.) .....	10
Data Retention Mode. ....	11
Power Down/Up Mode AC Waveforms (Figure 9.) .....	11
Power Down/Up AC Characteristics (Table 9.) .....	11
Power Down/Up Trip Points DC Characteristics (Table 10.) .....	12
V <sub>CC</sub> Noise And Negative Going Transients. ....	12
Supply Voltage Protection (Figure 10.) .....	12
<b>PART NUMBERING</b> .....	<b>13</b>
<b>PACKAGE MECHANICAL INFORMATION</b> .....	<b>14</b>
<b>REVISION HISTORY.</b> .....	<b>15</b>

**DESCRIPTION**

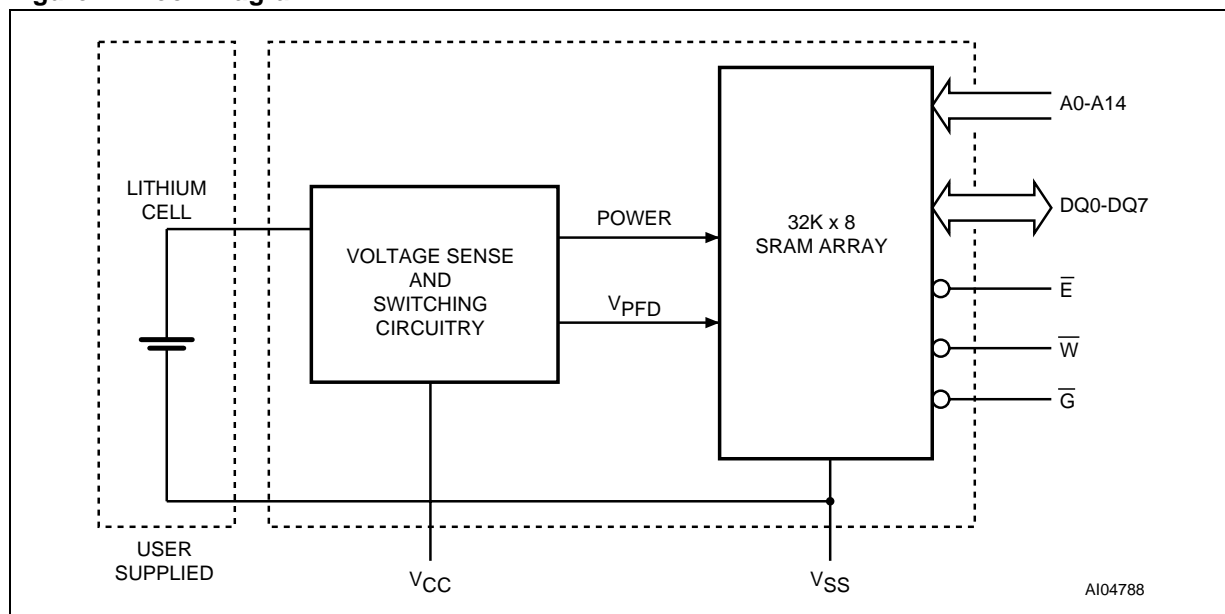
The M48Z32V ZEROPOWER<sup>®</sup> RAM is a 32 Kbit x 8, non-volatile static RAM that integrates power-fail deselect circuitry and battery control logic on a single die.

The 44-pin, 330mil SOIC provides a battery pin for an external, user-supplied battery. This is all that is required to fully non-volatize the SRAM.

**Figure 3. SOIC Connections**

Note: NF, Pin 7 must be tied to V<sub>SS</sub>.

Figure 4. Block Diagram



**MAXIMUM RATING**

Stressing the device above the rating listed in the “Absolute Maximum Ratings” table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is

not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

Table 2. Absolute Maximum Ratings

Symbol	Parameter	Value	Unit	
T <sub>A</sub>	Ambient Operating Temperature	Grade 1	0 to 70	°C
		Grade 6	-40 to 85	°C
T <sub>STG</sub>	Storage Temperature (V <sub>CC</sub> Off, Oscillator Off)	SOIC	-55 to 125	°C
T <sub>SLD</sub> <sup>(1)</sup>	Lead Solder Temperature for 10 seconds		260	°C
V <sub>IO</sub>	Input or Output Voltages		-0.3 to V <sub>CC</sub> + 0.3	V
V <sub>CC</sub>	Supply Voltage		-0.3 to 4.6	V
I <sub>O</sub>	Output Current		20	mA
P <sub>D</sub>	Power Dissipation		1	W

Note: 1. Reflow at peak temperature of 215°C to 225°C for < 60 seconds (total thermal budget not to exceed 180°C for between 90 and 120 seconds).

**CAUTION:** Negative undershoots below -0.3V are not allowed on any pin while in the Battery Back-up mode.

## DC AND AC PARAMETERS

This section summarizes the operating and measurement conditions, as well as the DC and AC characteristics of the device. The parameters in the following DC and AC Characteristic tables are derived from tests performed under the Measure-

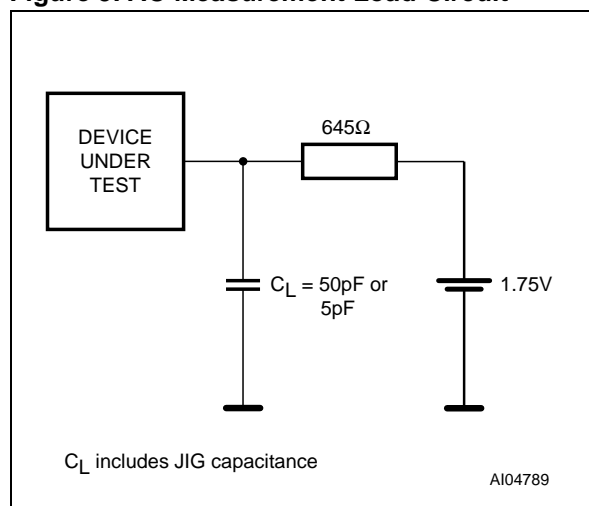
ment Conditions listed in the relevant tables. Designers should check that the operating conditions in their projects match the measurement conditions when using the quoted parameters.

**Table 3. Operating and AC Measurement Conditions**

Parameter <sup>(1)</sup>	M48Z32V	Unit
Supply Voltage ( $V_{CC}$ )	3.0 to 3.6	V
Ambient Operating Temperature ( $T_A$ )	Grade 1	0 to 70
	Grade 6	-40 to 85
Load Capacitance ( $C_L$ )	50	pF
Input Rise and Fall Times	$\leq 5$	ns
Input Pulse Voltages	0 to 3	V
Input and Output Timing Ref. Voltages	1.5	V

Note: 1. Output Hi-Z is defined as the point where data is no longer driven.

**Figure 5. AC Measurement Load Circuit**



**Table 4. Capacitance**

Symbol	Parameter <sup>(1,2)</sup>	Min	Max	Unit
$C_{IN}$	Input Capacitance		10	pF
$C_{IO}^{(3)}$	Input / Output Capacitance		10	pF

Note: 1. Effective capacitance measured with power supply at 3.3V; sampled only, not 100% tested.  
 2. At 25°C,  $f = 1\text{MHz}$ .  
 3. Outputs deselected.

Table 5. DC Characteristics

Sym	Parameter	Test Condition <sup>(1)</sup>	Min	Typ	Max	Unit
I <sub>LI</sub>	Input Leakage Current	$0V \leq V_{IN} \leq V_{CC}$			±1	μA
I <sub>LO</sub> <sup>(2)</sup>	Output Leakage Current	$0V \leq V_{OUT} \leq V_{CC}$			±1	μA
I <sub>BAT</sub>	Battery Current	T <sub>A</sub> = 40°C; V <sub>CC</sub> = 0V V <sub>BAT</sub> = 3V		0.2	1.2	μA
I <sub>CC1</sub>	Supply Current	I <sub>O</sub> = 0mA; Cycle Time = Min $\bar{E} = 0.2V$ , other input = V <sub>CC</sub> - 2V or 0.2V			45	mA
I <sub>CC2</sub>	Supply Current (TTL Standby)	$\bar{E} = V_{IH}$			800	μA
I <sub>CC3</sub>	Supply Current (CMOS Standby)	$\bar{E} = V_{CC} - 0.2V$			500	μA
V <sub>IL</sub> <sup>(3)</sup>	Input Low Voltage		-0.3		0.8	V
V <sub>IH</sub>	Input High Voltage		2.2		V <sub>CC</sub> + 0.3	V
V <sub>OL</sub>	Output Low Voltage	I <sub>OL</sub> = 2.1mA			0.4	V
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = -1mA	0.8V <sub>CC</sub>			V

Note: 1. Valid for Ambient Operating Temperature: T<sub>A</sub> = 0 to 70°C or -40 to 85°C; V<sub>CC</sub> = 3.0 to 3.6V (except where noted).

2. Outputs deselected.

3. Negative spikes of -1V allowed for up to 10ns once per cycle.

## OPERATING MODES

The M48Z32V also has its own Power-fail Detect circuit. The control circuitry constantly monitors the single power supply for an out of tolerance condition. When V<sub>CC</sub> is out of tolerance, the circuit write protects the SRAM, providing a high degree

of data security in the midst of unpredictable system operation brought on by low V<sub>CC</sub>. As V<sub>CC</sub> falls below approximately V<sub>SO</sub>, the control circuitry connects the battery which maintains data until valid power returns.

Table 6. Operating Modes

Mode	V <sub>CC</sub>	$\bar{E}$	$\bar{G}$	$\bar{W}$	DQ0-DQ7	Power
Deselect	3.0 to 3.6V	V <sub>IH</sub>	X	X	High Z	Standby
WRITE		V <sub>IL</sub>	X	V <sub>IL</sub>	D <sub>IN</sub>	Active
READ		V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	D <sub>OUT</sub>	Active
READ		V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IH</sub>	High Z	Active
Deselect	V <sub>SO</sub> to V <sub>PFD</sub> (min) <sup>(1)</sup>	X	X	X	High Z	CMOS Standby
Deselect	≤ V <sub>SO</sub> <sup>(1)</sup>	X	X	X	High Z	Battery Back-up Mode

Note: X = V<sub>IH</sub> or V<sub>IL</sub>; V<sub>SO</sub> = Battery Back-up Switchover Voltage.

1. See Table 10, page 12 for details.

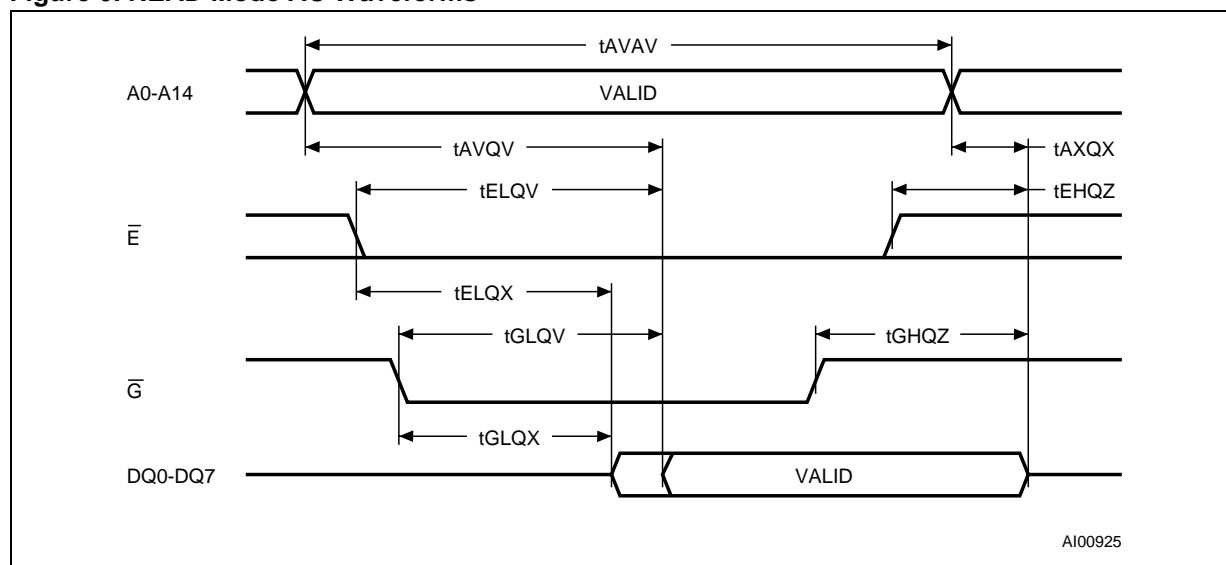
### READ Mode

The M48Z32V is in the READ Mode whenever  $\overline{W}$  (WRITE Enable) is high,  $\overline{E}$  (Chip Enable) is low. The device architecture allows ripple-through access of data from eight of 262,144 locations in the static storage array. Thus, the unique address specified by the 15 Address Inputs defines which one of the 32,768 bytes of data is to be accessed. Valid data will be available at the Data I/O pins within Address Access time ( $t_{AVQV}$ ) after the last address input signal is stable, providing that the  $\overline{E}$  and  $\overline{G}$  access times are also satisfied. If the  $\overline{E}$  and  $\overline{G}$  access times are not met, valid data will be

available after the latter of the Chip Enable Access time ( $t_{ELQV}$ ) or Output Enable Access time ( $t_{GLQV}$ ).

The state of the eight three-state Data I/O signals is controlled by  $\overline{E}$  and  $\overline{G}$ . If the outputs are activated before  $t_{AVQV}$ , the data lines will be driven to an indeterminate state until  $t_{AVQV}$ . If the Address Inputs are changed while  $\overline{E}$  and  $\overline{G}$  remain active, output data will remain valid for Output Data Hold time ( $t_{AXQX}$ ) but will go indeterminate until the next Address Access.

Figure 6. READ Mode AC Waveforms



Note: WRITE Enable ( $\overline{W}$ ) = High.

Table 7. READ Mode AC Characteristics

Symbol	Parameter <sup>(1)</sup>	M48Z32V		Unit
		-35		
		Min	Max	
t <sub>AVAV</sub>	READ Cycle Time	35		ns
t <sub>AVQV</sub>	Address Valid to Output Valid		35	ns
t <sub>ELQV</sub>	Chip Enable Low to Output Valid		35	ns
t <sub>GLQV</sub>	Output Enable Low to Output Valid		15	ns
t <sub>ELQX</sub> <sup>(2)</sup>	Chip Enable Low to Output Transition	5		ns
t <sub>GLQX</sub> <sup>(2)</sup>	Output Enable Low to Output Transition	0		ns
t <sub>EHQZ</sub> <sup>(2)</sup>	Chip Enable High to Output Hi-Z		13	ns
t <sub>GHQZ</sub> <sup>(2)</sup>	Output Enable High to Output Hi-Z		13	ns
t <sub>AXQX</sub>	Address Transition to Output Transition	5	0	ns

Note: 1. Valid for Ambient Operating Temperature: T<sub>A</sub> = 0 to 70°C or -40 to 85°C; V<sub>CC</sub> = 3.0 to 3.6V (except where noted).  
 2. C<sub>L</sub> = 5pF (see Figure 5, page 5).

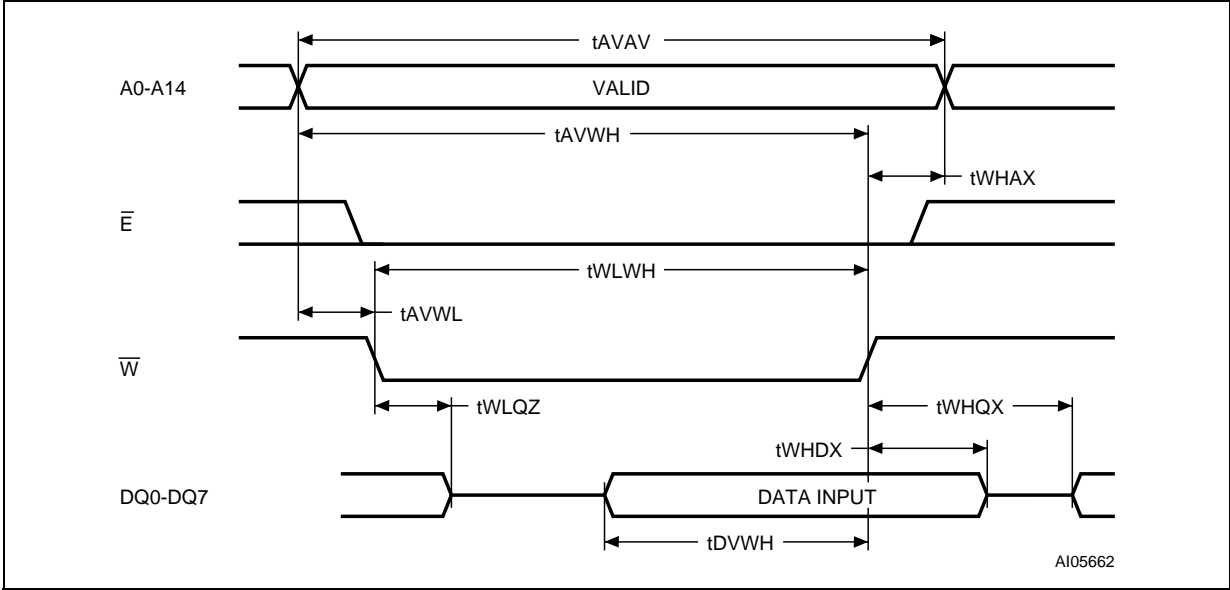


**WRITE Mode**

The M48Z32V is in the WRITE Mode whenever  $\overline{W}$  and  $\overline{E}$  are low. The start of a WRITE is referenced from the latter occurring falling edge of  $\overline{W}$  or  $\overline{E}$ . A WRITE is terminated by the earlier rising edge of  $\overline{W}$  or  $\overline{E}$ . The addresses must be held valid throughout the cycle.  $\overline{E}$  or  $\overline{W}$  must return high for a minimum of  $t_{EHAX}$  from Chip Enable or  $t_{WHAX}$  from WRITE Enable prior to the initiation of another

READ or WRITE cycle. Data-in must be valid  $t_{D-VWH}$  prior to the end of WRITE and remain valid for  $t_{WHDX}$  afterward.  $\overline{G}$  should be kept high during WRITE cycles to avoid bus contention; although, if the output bus has been activated by a low on  $\overline{E}$  and  $\overline{G}$ , a low on  $\overline{W}$  will disable the outputs  $t_{WLQZ}$  after  $\overline{W}$  falls.

**Figure 7. WRITE Enable Controlled, WRITE Mode AC Waveforms**



**Figure 8. Chip Enable Controlled, WRITE Mode AC Waveforms**

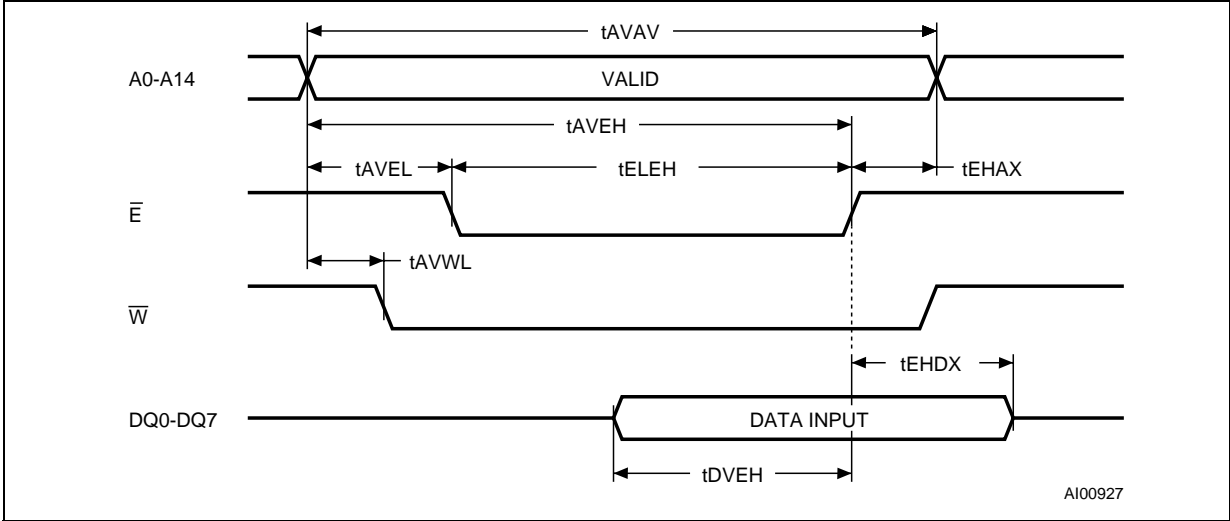


Table 8. WRITE Mode AC Characteristics

Symbol	Parameter <sup>(1)</sup>	M48Z32V		Unit
		-35		
		Min	Max	
t <sub>AVAV</sub>	WRITE Cycle Time	35		ns
t <sub>AVWL</sub>	Address Valid to WRITE Enable Low	0		ns
t <sub>AVEL</sub>	Address Valid to Chip Enable Low	0		ns
t <sub>WLWH</sub>	WRITE Enable Pulse Width	25		ns
t <sub>ELEH</sub>	Chip Enable Low to Chip Enable High	25		ns
t <sub>WHAX</sub>	WRITE Enable High to Address Transition	0		ns
t <sub>EHAX</sub>	Chip Enable High to Address Transition	0		ns
t <sub>DVWH</sub>	Input Valid to WRITE Enable High	12		ns
t <sub>DVEH</sub>	Input Valid to Chip Enable High	12		ns
t <sub>WHDX</sub>	WRITE Enable High to Input Transition	0		ns
t <sub>EHDX</sub>	Chip Enable High to Input Transition	0		ns
t <sub>WLQZ</sub> <sup>(2,3)</sup>	WRITE Enable Low to Output Hi-Z		13	ns
t <sub>AVWH</sub>	Address Valid to WRITE Enable High	25		ns
t <sub>AVEH</sub>	Address Valid to Chip Enable High	25		ns
t <sub>WHQX</sub> <sup>(2,3)</sup>	WRITE Enable High to Output Transition	5		ns

Note: 1. Valid for Ambient Operating Temperature: T<sub>A</sub> = 0 to 70°C or -40 to 85°C; V<sub>CC</sub> = 3.0 to 3.6V (except where noted).

2. C<sub>L</sub> = 5pF (see Figure 5, page 5).

3. If  $\bar{E}$  goes low simultaneously with  $\bar{W}$  going low, the outputs remain in the high impedance state.

### Data Retention Mode

With valid  $V_{CC}$  applied, the M48Z32V operates as a conventional BYTEWIDE™ static RAM. Should the supply voltage decay, the RAM will automatically power-fail deselect, write protecting itself when  $V_{CC}$  falls within the  $V_{PFD}(\max)$ ,  $V_{PFD}(\min)$  window. All outputs become high impedance, and all inputs are treated as “Don't care.”

**Note:** A power failure during a WRITE cycle may corrupt data at the currently addressed location, but does not jeopardize the rest of the RAM's content. At voltages below  $V_{PFD}(\min)$ , the user can be assured the memory will be in a write protected state, provided the  $V_{CC}$  fall time is not less than  $t_F$ . The M48Z32V may respond to transient noise spikes on  $V_{CC}$  that reach into the deselect window

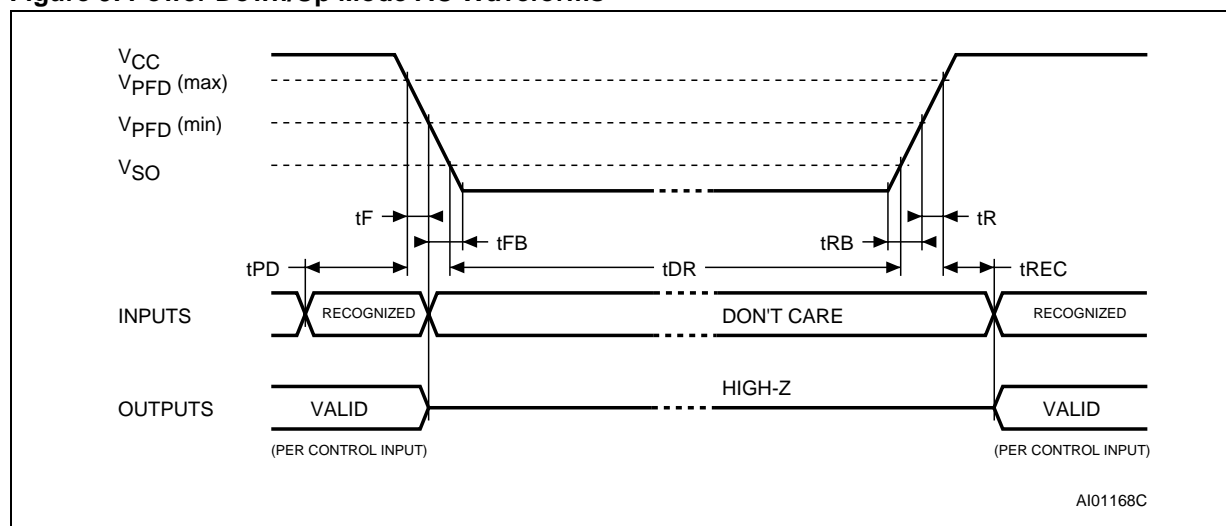
during the time the device is sampling  $V_{CC}$ . Therefore, decoupling of the power supply lines is recommended.

When  $V_{CC}$  drops below  $V_{SO}$ , the control circuit switches power to the external battery which preserves data.

As system power returns and  $V_{CC}$  rises above  $V_{SO}$ , the battery is disconnected, and the power supply is switched to external  $V_{CC}$ . Write protection continues until  $V_{CC}$  reaches  $V_{PFD}(\min)$  plus  $t_{REC}(\min)$ . Normal RAM operation can resume  $t_{REC}$  after  $V_{CC}$  exceeds  $V_{PFD}(\max)$ .

For more information on Battery Storage Life refer to the Application Note AN1012.

**Figure 9. Power Down/Up Mode AC Waveforms**



**Table 9. Power Down/Up AC Characteristics**

Symbol	Parameter <sup>(1)</sup>	Min	Max	Unit
$t_{PD}$	$\bar{E}$ or $\bar{W}$ at $V_{IH}$ before Power Down	0		$\mu s$
$t_F^{(2)}$	$V_{PFD}(\max)$ to $V_{PFD}(\min)$ $V_{CC}$ Fall Time	300		$\mu s$
$t_{FB}^{(3)}$	$V_{PFD}(\min)$ to $V_{SS}$ $V_{CC}$ Fall Time	10		$\mu s$
$t_R$	$V_{PFD}(\min)$ to $V_{PFD}(\max)$ $V_{CC}$ Rise Time	10		$\mu s$
$t_{RB}$	$V_{SS}$ to $V_{PFD}(\min)$ $V_{CC}$ Rise Time	1		$\mu s$
$t_{REC}^{(4)}$	$V_{PFD}(\max)$ to Inputs Recognized	40	200	ms

Note: 1. Valid for Ambient Operating Temperature:  $T_A = 0$  to  $70^\circ C$  or  $-40$  to  $85^\circ C$ ;  $V_{CC} = 3.0$  to  $3.6V$  (except where noted).

2.  $V_{PFD}(\max)$  to  $V_{PFD}(\min)$  fall time of less than  $t_F$  may result in deselection/write protection not occurring until  $200\mu s$  after  $V_{CC}$  passes  $V_{PFD}(\min)$ .

3.  $V_{PFD}(\min)$  to  $V_{SS}$  fall time of less than  $t_{FB}$  may cause corruption of RAM data.

4.  $t_{REC}(\min) = 20ms$  for industrial temperature Grade (6) device.

**Table 10. Power Down/Up Trip Points DC Characteristics**

Symbol	Parameter <sup>(1,2)</sup>	Min	Typ	Max	Unit
V <sub>PFD</sub>	Power-fail Deselect Voltage	2.7	2.85	3.0	V
V <sub>SO</sub>	Battery Back-up Switchover Voltage		V <sub>PFD</sub> – 100mV		V

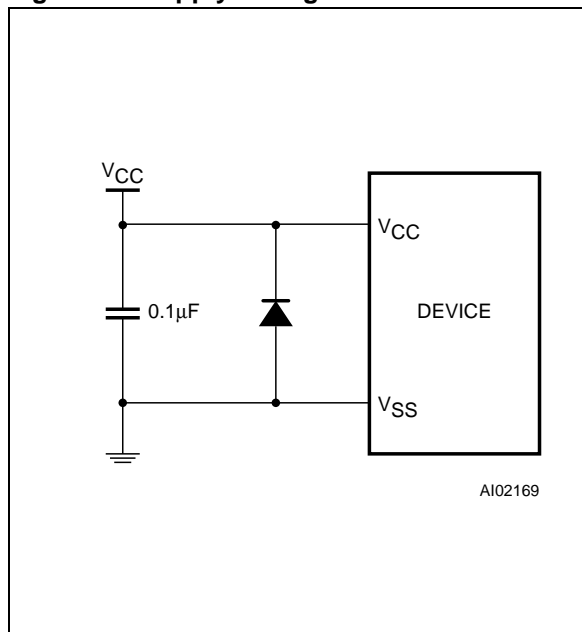
Note: 1. All voltages referenced to V<sub>SS</sub>.  
 2. Valid for Ambient Operating Temperature: T<sub>A</sub> = 0 to 70°C or –40 to 85°C; V<sub>CC</sub> = 3.0 to 3.6V (except where noted).

**V<sub>CC</sub> Noise And Negative Going Transients**

I<sub>CC</sub> transients, including those produced by output switching, can produce voltage fluctuations, resulting in spikes on the V<sub>CC</sub> bus. These transients can be reduced if capacitors are used to store energy which stabilizes the V<sub>CC</sub> bus. The energy stored in the bypass capacitors will be released as low going spikes are generated or energy will be absorbed when overshoots occur. A ceramic bypass capacitor value of 0.1µF (see Figure 10) is recommended in order to provide the needed filtering.

In addition to transients that are caused by normal SRAM operation, power cycling can generate negative voltage spikes on V<sub>CC</sub> that drive it to values below V<sub>SS</sub> by as much as one volt. These negative spikes can cause data corruption in the SRAM while in battery backup mode. To protect from these voltage spikes, ST recommends connecting a schottky diode from V<sub>CC</sub> to V<sub>SS</sub> (cathode connected to V<sub>CC</sub>, anode to V<sub>SS</sub>). (Schottky diode 1N5817 is recommended for through hole and MBRS120T3 is recommended for surface mount).

**Figure 10. Supply Voltage Protection**



## PART NUMBERING

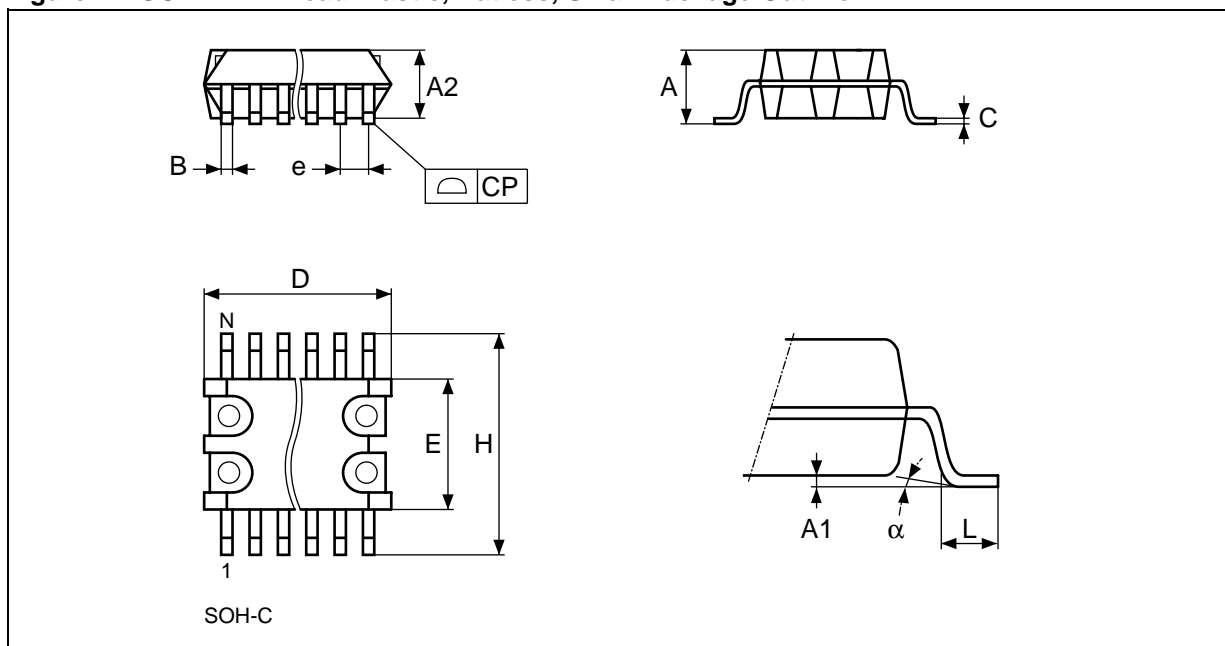
Table 11. Ordering Information Scheme

Example:	M48Z	32V	-35	MT	1	TR
<b>Device Type</b>	M48Z					
<b>Supply Voltage and Write Protect Voltage</b>		32V = $V_{CC} = 3.0$ to $3.6V$ ; $V_{PFD} = 2.7$ to $3.0V$				
<b>Speed</b>			-35 = 35ns			
<b>Package</b>				MT = 44-lead, Hatless SOIC		
<b>Temperature Range</b>					1 = 0 to 70°C 6 = -40 to 85°C	
<b>Shipping Method for SOIC</b>						blank = Tubes TR = Tape & Reel

For a list of available options (e.g., Speed, Package) or for further information on any aspect of this device, please contact the ST Sales Office nearest to you.

PACKAGE MECHANICAL INFORMATION

Figure 11. SOH44 – 44-lead Plastic, Hatless, Small Package Outline



Note: Drawing is not to scale.

Table 12. SOH44 – 44-lead Plastic, Hatless, Small Package Mechanical Data

Symbol	mm			inch		
	Typ	Min	Max	Typ	Min	Max
A			3.05			0.120
A1		0.05	0.36		0.002	0.014
A2		2.34	2.69		0.092	0.106
B		0.36	0.46		0.014	0.018
C		0.15	0.32		0.006	0.012
D		17.71	18.49		0.697	0.728
E		8.23	8.89		0.324	0.350
e	0.81	–	–	0.032	–	–
H		11.51	12.70		0.453	0.500
L		0.41	1.27		0.016	0.050
alpha		0°	8°		0°	8°
N	44			44		
CP			0.10			0.004

---

**REVISION HISTORY****Table 13. Revision History**

Date	Rev. #	Revision Details
October 2002	1.0	First Issue
11/07/02	1.1	Update Absolute Maximum Ratings, DC Characteristics (Table 2, 5)

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is registered trademark of STMicroelectronics  
All other names are the property of their respective owners.

© 2002 STMicroelectronics - All Rights Reserved

STMicroelectronics GROUP OF COMPANIES  
Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia -  
Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

[www.st.com](http://www.st.com)